

isc N-Channel MOSFET Transistor

IRF730B

DESCRIPTION

- Drain Current $-I_D=5.5A@ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}= 400V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 1.0 \Omega (\text{Max})$
- Fast Switching Speed

APPLICATIONS

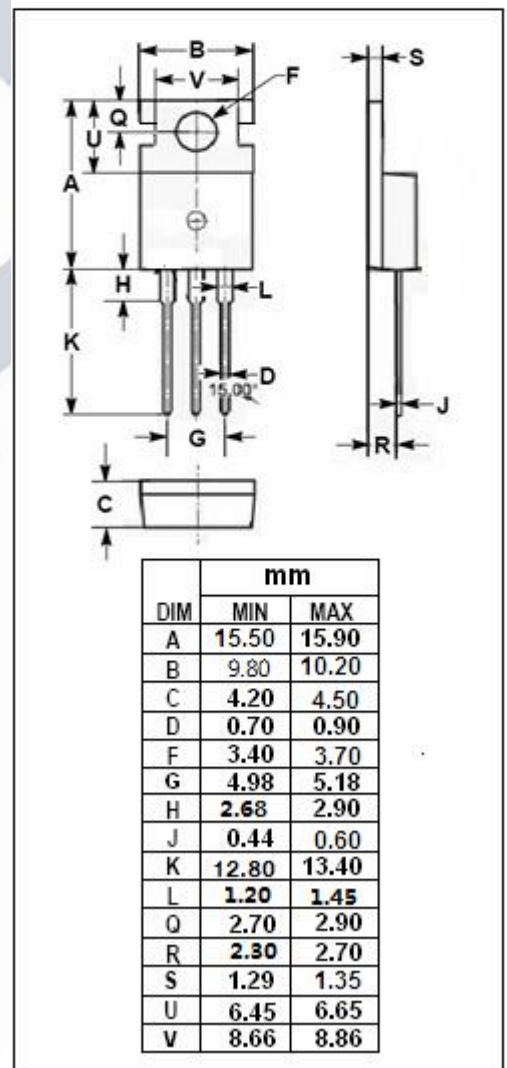
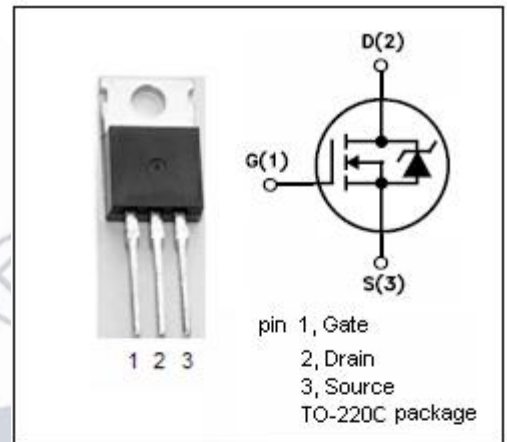
- Designed especially for high voltage,high speed applications, such as off-line switching power supplies , UPS,AC and DC motor controls,relay and solenoid drivers.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	400	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $TC=25^\circ C$	5.5	A
P_{tot}	Total Dissipation@ $TC=25^\circ C$	73	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	1.71	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	62.5	$^\circ C/W$



isc N-Channel Mosfet Transistor**IRF730B****• ELECTRICAL CHARACTERISTICS (T_c=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 0.25mA	400		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 0.25mA	2	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D =2.75A		1.0	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 400V; V _{GS} = 0		10	uA
V _{SD}	Diode Forward Voltage	I _F = 5.5A; V _{GS} = 0		1.5	V